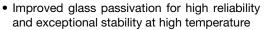


Medium Power Phase Control Thyristors (Stud Version), 16 A



PRODUCT SUMMARY				
Package	TO-48 (TO-208AA)			
Diode variation	Single SCR			
I _{T(AV)}	16 A			
V _{DRM} /V _{RRM}	100 V to 1200 V			
V _{TM}	1.75 V			
I _{GT}	60 mA			
TJ	- 65 °C to 125 °C			

FEATURES





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- · Designed and qualified for industrial and consumer level
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- · Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		16	A		
I _{T(AV)}	T _C	85	°C		
I _{T(RMS)}		35	A		
	50 Hz	340	Δ.		
ITSM	60 Hz	360	A		
12.	50 Hz	574	A ² s		
I ² t	60 Hz	524			
V _{DRM} /V _{RRM}		100 to 1200	V		
tq	Typical	110	μs		
T _J		- 65 to 125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{AT T}_{J} &= T_{J} & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$			
	10	100	150	20			
	20	200	300				
	40	400	500				
16RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

⁽²⁾ For voltage pulses with $t_p \le 5$ ms



PARAMETER	SYMBOL		TEST COND	ITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	180° sinusoi	180° sinusoidal conduction		16	Α
at case temperature	1(~v)				85	°C
Maximum RMS on-state current	I _{T(RMS)}				35	Α
		t = 10 ms	No voltage		340	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		360	٨
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		285	Α
		t = 8.3 ms	reapplied	Sinusoidal half wave,	300	
Maximum I ² t for fusing		t = 10 ms	No voltage	initial T _J = T _J maximum	574	A ² s
	101	t = 8.3 ms	reapplied		524	
	l ² t	t = 10 ms	100 % V _{RRM} reapplied		405	
		t = 8.3 ms			375	
Maximum I ² √t for fusing	I²√t		t = 0.1 to 10 ms, no voltage reapplied, T _J = T _J maximum		5740	A²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $I_{J} = I_{J}$ maximum		0.97	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		1.24	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $I_{J} = I_{J}$ maximum		17.9	m()	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		13.6	mΩ	
Maximum on-state voltage	V_{TM}	I _{pk} = 50 A, T _J = 25 °C			1.75	V
Maximum holding current	I _H	T 05 °C -	anada ayınalı (C.V. :	reciptive lead	130	A
Latching current	ΙL	T_J = 25 °C, anode supply 6 V, resistive load		200	- mA	

SWITCHING					
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS
	$V_{DRM} \leq 600 \ V$			200	
Maximum rate of rise	$V_{DRM} \leq 800 \ V$	dl/dt	$T_J = T_J$ maximum, $V_{DM} =$ Rated V_{DRM} Gate pulse = 20 V, 15 Ω , $t_p = 6$ μ s, $t_r = 0.1$ μ s maximum $I_{TM} = (2 \text{ x rated dI/dt})$ A	180	- A/μs
	$V_{DRM} \leq 1000 \; V$	ui/ut		160	
	$V_{DRM} \leq 1600 \; V$			150	
Typical turn-on time		t _{gt}	$T_J = 25 ^{\circ}\text{C}$, at rated V_{DRM}/V_{RRM} , $T_J = 125 ^{\circ}\text{C}$	0.9	
Typical reverse recovery time		t _{rr}	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200 \mu s$, $dI/dt = -10 A/\mu s$	4	μs
Typical turn-off time		t _q	$T_J=T_J$ maximum, $I_{TM}=I_{T(AV)},t_p>200~\mu s,V_R=100~V,dI/dt=$ - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W	110	

Note

• t_q = 10 μs up to 600 V, t_q = 30 μs up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	T _J = T _J maximum linear to 100 % rated V _{DRM}	100	V/µs
of off-state voltage	uv/dt	T _J = T _J maximum linear to 67 % rated V _{DRM}	300 (1)	ν/μδ

Note

 $^{^{(1)}}$ Available with: $dV/dt = 1000 \ V/\mu s$, to complete code add S90 i.e. 16RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P_{GM}	T - T movimum		8.0	w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum		2.0] vv
Maximum peak positive gate current	I _{GM}	T _J = T _J maximum		1.5	Α
Maximum peak negative gate voltage	-V _{GM}	T _J = T _J maximum		10	V
	I _{GT}	T _J = - 65 °C	Maximum required gate trigger current/voltage are the lowest	90	mA
DC gate current required to trigger		T _J = 25 °C		60	
		T _J = 125 °C		35	
		T _J = - 65 °C	6 v anode to cathode applied	3.0	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.0	V
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated value		2.0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
Maximum operating junction and storage temperature range	T _J , T _{Stg}		- 65 t	o 125	°C
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.	86	K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased 0.35		35	10,00
		TO NUT	TO DEVICE		
			20 (27.5)	25	lbf ⋅ in
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m
		(ton labilitation amount)	2.3 (3.1)	2.8	N·m
Aira -tirabt			1	4	g
Approximate weight			0.	49	OZ.
Case style		See dimensions - link at the end of datasheet	TO-	208AA (TO-48)

△R _{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.21	0.15		
120°	0.25	0.25		
90°	0.31	0.34	$T_J = T_J \text{ maximum}$	K/W
60°	0.45	0.47		
30°	0.76	0.76		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

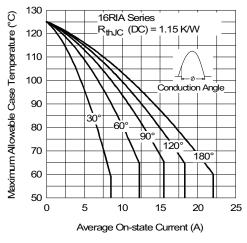


Fig. 1 - Current Ratings Characteristics

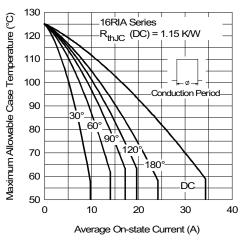


Fig. 2 - Current Ratings Characteristics

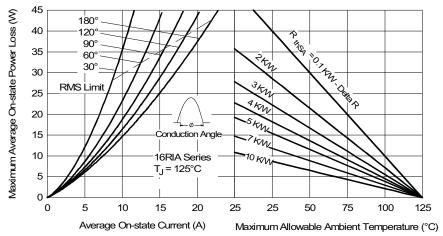


Fig. 3 - On-State Power Loss Characteristics

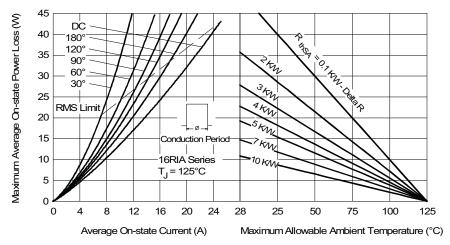


Fig. 4 - On-State Power Loss Characteristics

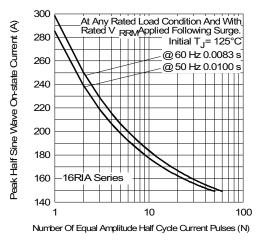


Fig. 5 - Maximum Non-Repetitive Surge Current

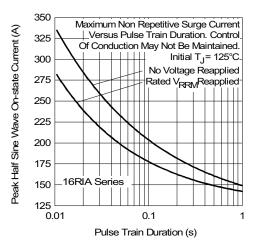


Fig. 6 - Maximum Non-Repetitive Surge Current

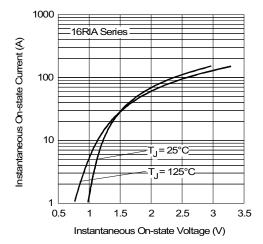


Fig. 7 - Forward Voltage Drop Characteristics

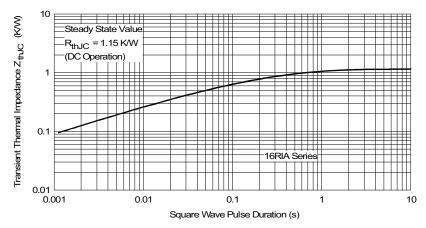


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



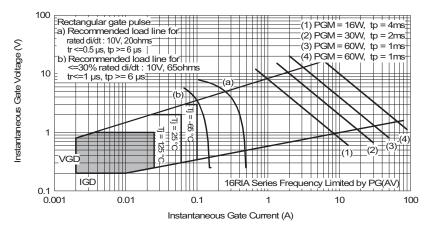
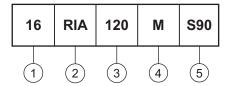


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



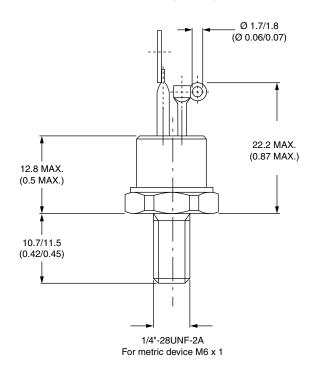
- 1 Current code
- Essential part number
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A
 M = Stud base TO-208AA (TO-48) M6 x 1
- Critical dV/dt:
 None = 300 V/μs (standard value)
 S90 = 1000 V/μs (special selection)

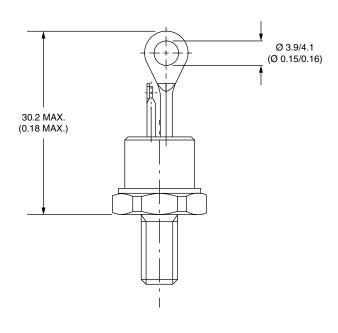
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

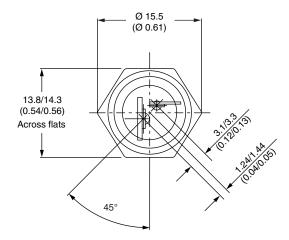


TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)









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